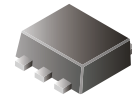


## CDSH6-16-G

### RoHS Device



### Features

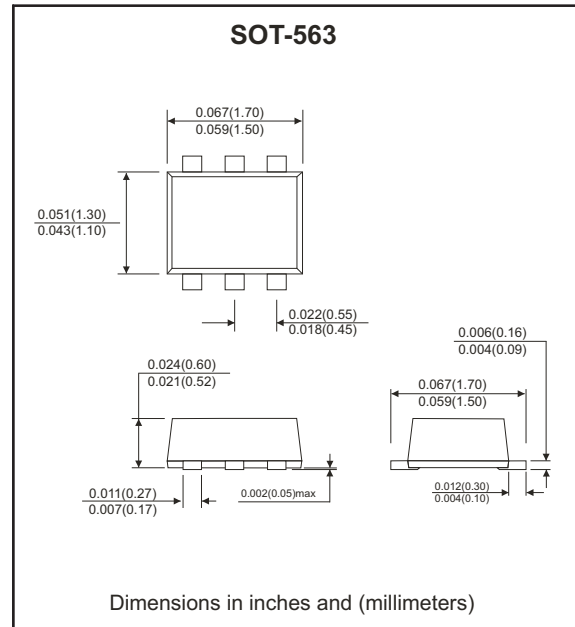
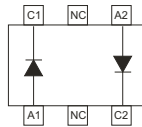
- Fast Switching Speed
- For general purpose switching applications.
- High conductance.

### Mechanical data

- Case: SOT-563, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208

### Marking: KAM

### Circuit diagram



### Maximum Ratings (at TA=25°C unless otherwise noted)

Parameter	Symbol	Max	Unit
Non-repetitive peak reverse voltage	$V_{RM}$	100	V
Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	75	V
RMS reverse voltage	$V_{R(RMS)}$	53	V
Forward continuous current	$I_{FM}$	300	mA
Averaged rectified output current	$I_o$	200	mA
Peak forward surge current @t=1.0µs @T=1.0s	$I_{FSM}$	2 1	A
Power dissipation	$P_D$	150	mW
Thermal resistance, junction to air	$R_{\theta JA}$	833	°C/W
Junction temperature	$T_J$	150	°C
Storage temperature	$T_{STG}$	-65 to +150	°C

### Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Max	Unit
Reverse breakdown voltage	$I_R=100\mu A$	$V_{BR}$	75		V
Reverse voltage leakage current	$V_R=75V$ $V_R=20V$	$I_R$		1 25	µA nA
Forward voltage	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$	$V_F$		0.715 0.855 1 1.25	V
Diode capacitance	$V_R=0V, f=1MHz$	$C_T$		2	pF
Reverse recovery time	$I_F=I_R=10mA, I_{rr}=0.1 \times I_R, R_L=100\Omega$	$t_{rr}$		4	nS

## Typical Characteristics (CDSH6-16-G)

Fig.1 - Forward Power Derating Curve

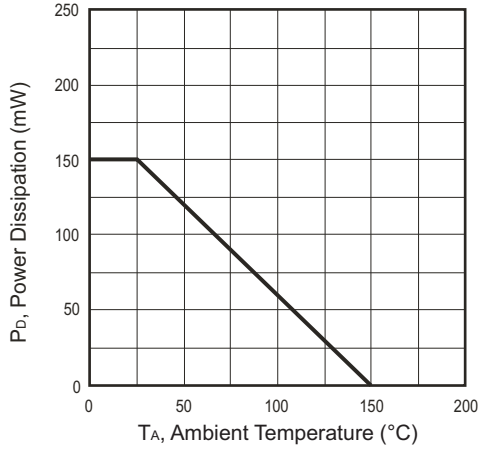


Fig.2 - Typical Forward Characteristics

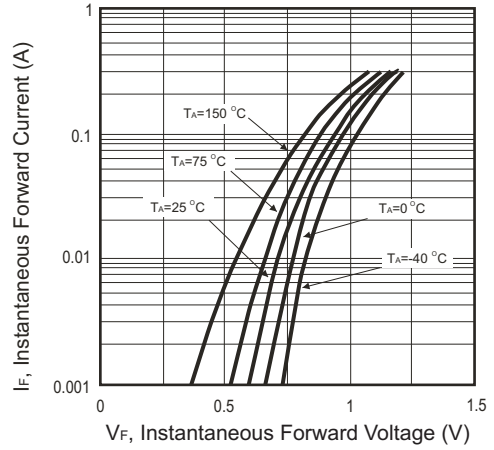


Fig.3 - Typical Diode Capacitance Characteristics

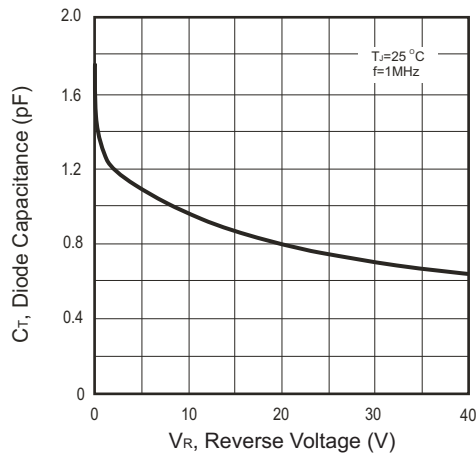


Fig.4 - Typical Reverse Current Characteristics

